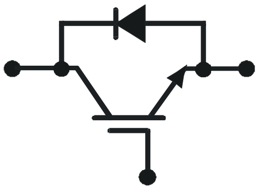
V_{CE} = 3300 V
I_C = 800 A



HiPak

IGBT Module
5SNA 0800N330100

Doc. No. 5SYA 1591-03 10-2020

- **Low-loss, rugged SPT chip-set**
- **Smooth switching SPT chip-set for good EMC**
- **Industry standard package**
- **High power density**
- **AlSiC base-plate for high power cycling capability**
- **AlN substrate for low thermal resistance**
- **Improved high reliability package**
- **Recognized under UL1557, File E196689**

Maximum rated values [1]

Parameter	Symbol	Conditions	min	max	Unit
Collector-emitter voltage	V_{CES}	V_{GE} = 0 V, $T_{vj} \geq 25$ °C		3300	V
DC collector current	I_C	T_c = 80 °C		800	A
Peak collector current	I_{CM}	t_p = 1 ms, T_c = 80 °C		1600	A
Gate-emitter voltage	V_{GES}		-20	20	V
Total power dissipation	P_{tot}	T_c = 25 °C, per switch (IGBT)		7700	W
DC forward current	I_F			800	A
Peak forward current	I_{FRM}			1600	A
Surge current	I_{FSM}	V_R = 0 V, T_{vj} = 125 °C, t_p = 10 ms, half-sinewave		8000	A
IGBT short circuit SOA	t_{psc}	V_{CC} = 2500 V, $V_{CEM\,CHIP} \leq 3300$ V $V_{GE} \leq 15$ V, $T_{vj} \leq 125$ °C		10	µs
Isolation voltage	V_{isol}	1 min, f = 50 Hz		6000	V
Junction temperature	T_{vj}			150	°C
Junction operating temperature	$T_{vj(op)}$		-50	125	°C
Case temperature	T_c		-50	125	°C
Storage temperature	T_{stg}		-50	125	°C
Mounting torques [2]	M_s	Base-heatsink, M6 screws	4	6	Nm
	M_{t1}	Main terminals, M8 screws	8	10	
	M_{t2}	Auxiliary terminals, M4 screws	2	3	

[1] Maximum rated values indicate limits beyond which damage to the device may occur per IEC 60747
[2] For detailed mounting instructions refer to document no. 5SYA 2039 - 01

IGBT characteristic values [3]

Parameter	Symbol	Conditions		min	typ	max	Unit
Collector (-emitter) breakdown voltage	$V_{(BR)CES}$	V_{GE} = 0 V, I_C = 10 mA, T_{vj} = 25 °C		3300			V
Collector-emitter saturation voltage [4]	$V_{CE\ sat}$	I_C = 800 A, V_{GE} = 15 V	T_{vj} = 25 °C	2.7	3.1	3.4	V
			T_{vj} = 125 °C	3.5	3.8	4.3	V
Collector cut-off current	I_{CES}	V_{CE} = 3300 V, V_{GE} = 0 V	T_{vj} = 25 °C			8	mA
			T_{vj} = 125 °C			80	mA
Gate leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V, T_{vj} = 125 °C		-500		500	nA
Gate-emitter threshold voltage	$V_{GE(TO)}$	I_C = 160 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		5.5		7.5	V
Gate charge	Q_{ge}	I_C = 800 A, V_{CE} = 1800 V, V_{GE} = -15 V .. 15 V			8.07		µC
Input capacitance	C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz, T_{vj} = 25 °C			125		nF
Output capacitance	C_{oes}				7.71		
Reverse transfer capacitance	C_{res}				1.48		
Turn-on delay time	$t_{d(on)}$	V_{CC} = 1800 V, I_C = 800 A, R_G = 2.2 Ω, V_{GE} = ±15 V, L_σ = 100 nH, inductive load	T_{vj} = 25 °C		525		ns
			T_{vj} = 125 °C		525		
Rise time	t_r		T_{vj} = 25 °C		190		ns
			T_{vj} = 125 °C		200		
Turn-off delay time	$t_{d(off)}$	V_{CC} = 1800 V, I_C = 800 A, R_G = 2.2 Ω, V_{GE} = ±15 V, L_σ = 100 nH, inductive load	T_{vj} = 25 °C		1060		ns
			T_{vj} = 125 °C		1210		
Fall time	t_f		T_{vj} = 25 °C		340		ns
			T_{vj} = 125 °C		460		
Turn-on switching energy	E_{on}	V_{CC} = 1800 V, I_C = 800 A, V_{GE} = ±15 V, R_G = 2.2 Ω, L_σ = 100 nH, inductive load	T_{vj} = 25 °C		1000		mJ
			T_{vj} = 125 °C		1380		
Turn-off switching energy	E_{off}	V_{CC} = 1800 V, I_C = 800 A, V_{GE} = ±15 V, R_G = 2.2 Ω, L_σ = 100 nH, inductive load	T_{vj} = 25 °C		880		mJ
			T_{vj} = 125 °C		1250		
Short circuit current	I_{SC}	t_{psc} ≤ 10 µs, V_{GE} = 15 V, T_{vj} = 125 °C, V_{CC} = 2500 V, $V_{CEM\ CHIP}$ ≤ 3300 V			3300		A
Module stray inductance	$L_{\sigma\ CE}$				15		nH
Resistance, terminal-chip	$R_{CC'+EE'}$		T_C = 25 °C		0.09		mΩ
			T_C = 125 °C		0.13		

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[3] Characteristic values according to IEC 60747 – 9

[4] Collector-emitter saturation voltage is given at chip level

Diode characteristic values 5)

Parameter	Symbol	Conditions		min	typ	max	Unit
Forward voltage 6)	V_F	I_F = 800 A	T_{vj} = 25 °C	2.0	2.3	2.6	V
			T_{vj} = 125 °C	2.0	2.35	2.6	
Reverse recovery current	I_{rr}	V_{CC} = 1800 V, I_F = 800 A, V_{GE} = ±15 V, R_G = 2.2 Ω L_σ = 100 nH inductive load	T_{vj} = 25 °C		710		A
			T_{vj} = 125 °C		950		
Recovered charge	Q_{rr}		T_{vj} = 25 °C		500		µC
			T_{vj} = 125 °C		930		
Reverse recovery time	t_{rr}		T_{vj} = 25 °C		850		ns
			T_{vj} = 125 °C		1550		
Reverse recovery energy	E_{rec}		T_{vj} = 25 °C		620		mJ
			T_{vj} = 125 °C		1180		

5) Characteristic values according to IEC 60747 – 2
6) Forward voltage is given at chip level

Thermal properties 7)

Parameter	Symbol	Conditions	min	typ	max	Unit
IGBT thermal resistance junction to case	$R_{th(j-c)IGBT}$				0.013	K/W
Diode thermal resistance junction to case	$R_{th(j-c)DIODE}$				0.025	K/W
IGBT thermal resistance case to heatsink 2)	$R_{th(c-s)IGBT}$	IGBT per switch, λ grease = 1W/m × K		0.012		K/W
Diode thermal resistance case to heatsink 7)	$R_{th(c-s)DIODE}$	Diode per switch, λ grease = 1W/m × K		0.024		K/W

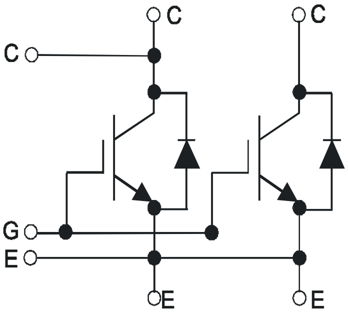
2) For detailed mounting instructions refer to document no. 5SYA 2039 - 01

Mechanical properties 7)

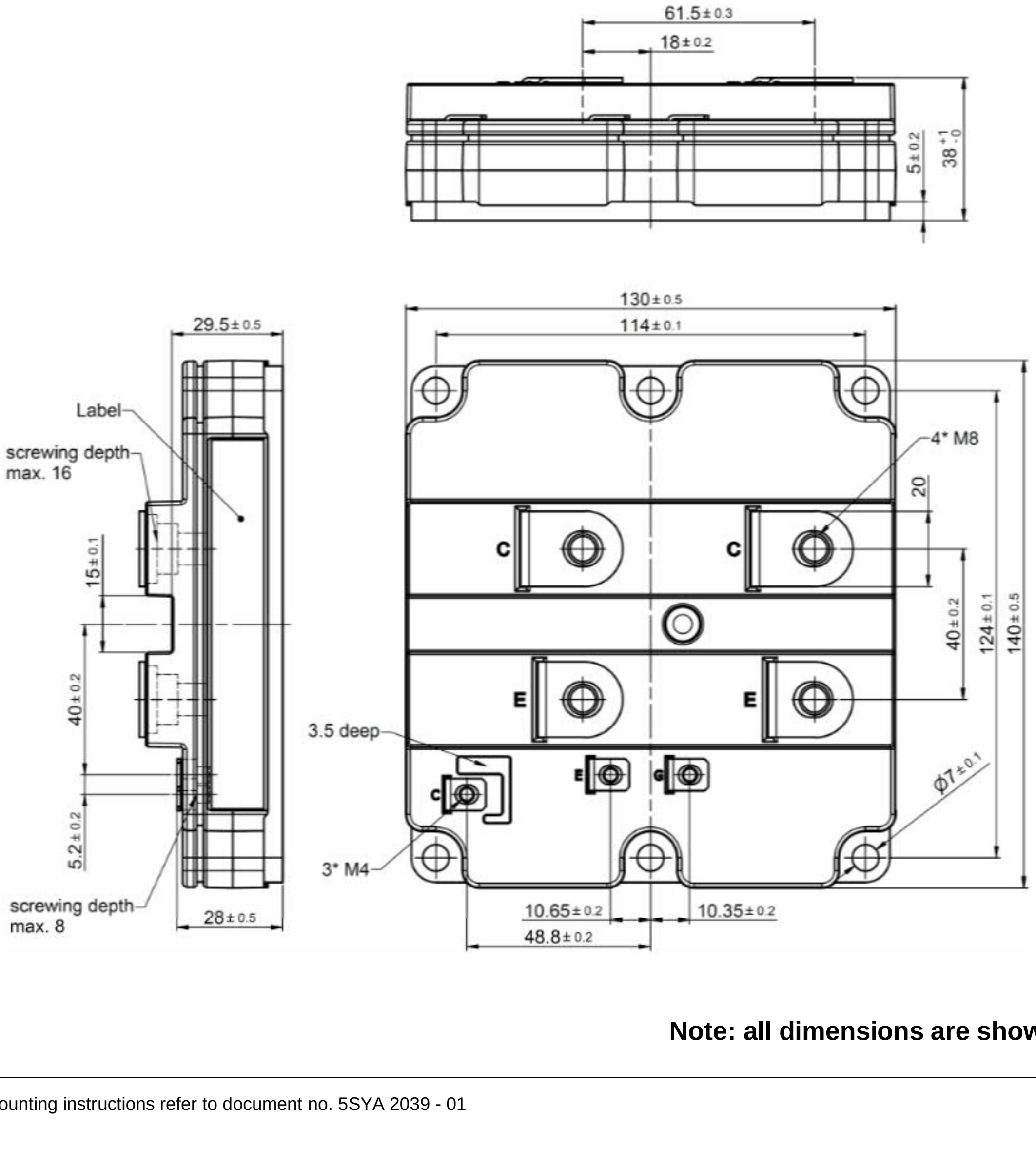
Parameter	Symbol	Conditions		min	typ	max	Unit
Dimensions	L × W × H	Typical , see outline drawing		130 × 140 × 38			mm
Comparative tracking index	CTI			600			
Clearance distance in air	d_a	according to IEC 60664-1 and EN 50124-1	Term. to base:	19			mm
			Term. to term:	19			
Surface creepage distance	d_s	according to IEC 60664-1 and EN 50124-1	Term. to base:	28.2			mm
			Term. to term:	28.2			
Mass	m				820		g

7) Thermal and mechanical properties according to IEC 60747 – 15

Electrical configuration



Outline drawing [2)]



Note: all dimensions are shown in mm

[2)] For detailed mounting instructions refer to document no. 5SYA 2039 - 01

This is an electrostatic sensitive device, please observe the international standard IEC 60747-1, chap. IX. This product has been designed and qualified for industrial level.

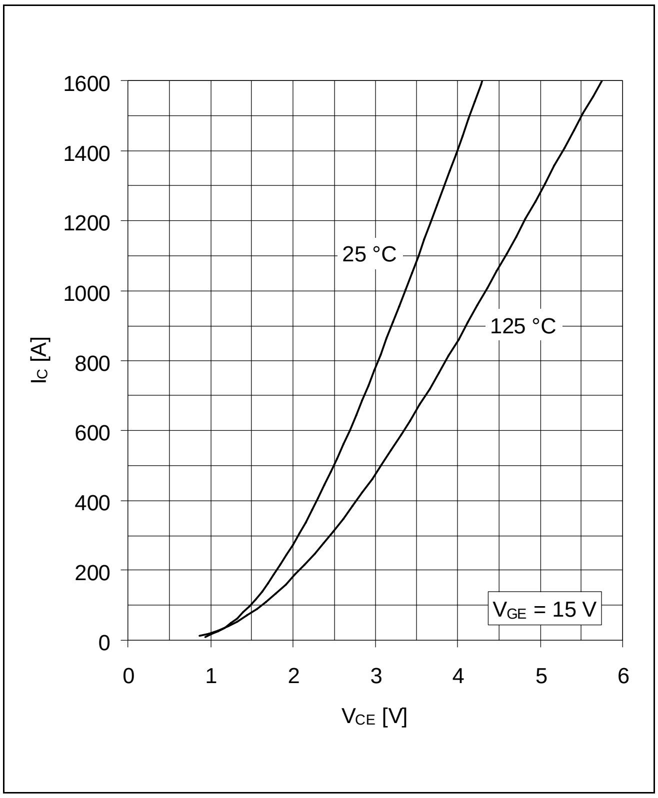


Fig. 1 Typical on-state characteristics, chip level

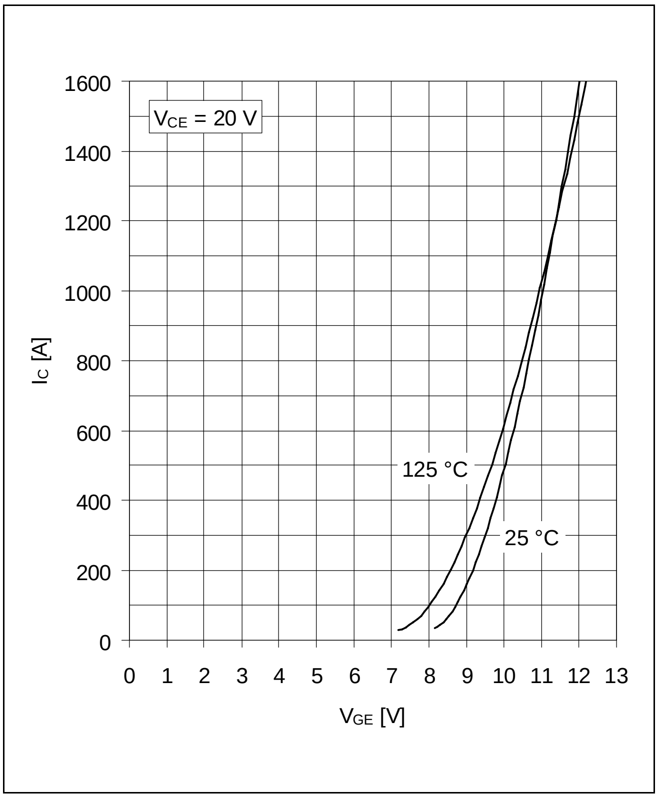


Fig. 2 Typical transfer characteristics, chip level

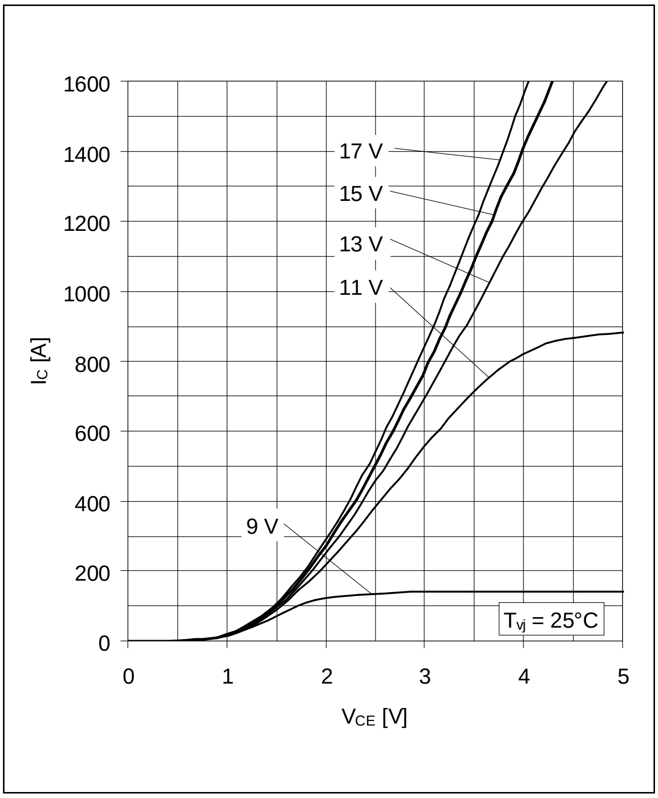


Fig. 3 Typical output characteristics, chip level

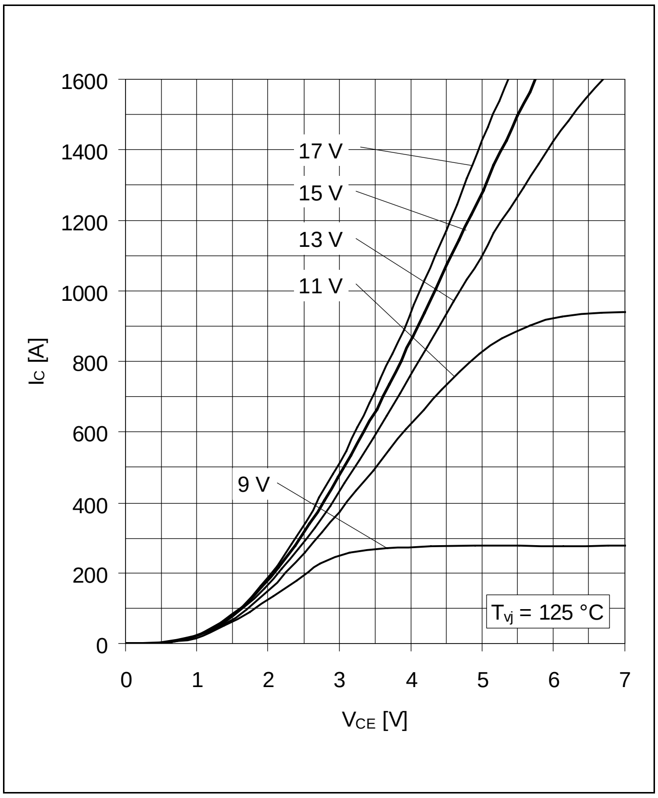
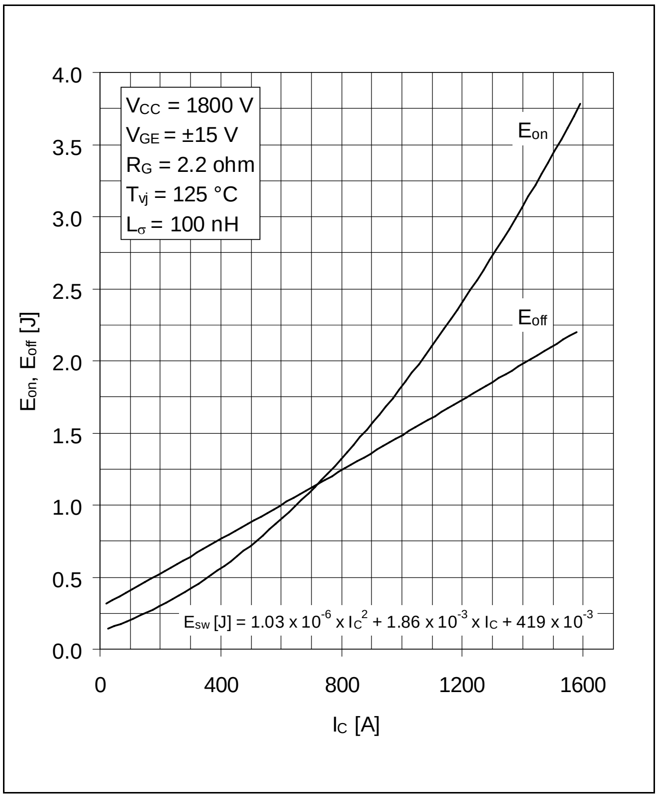


Fig. 4 Typical output characteristics, chip level



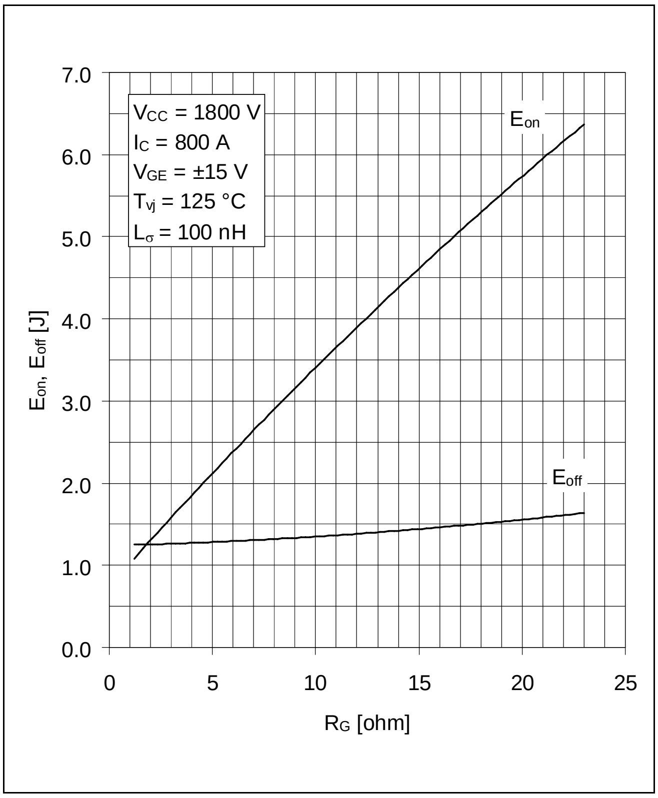
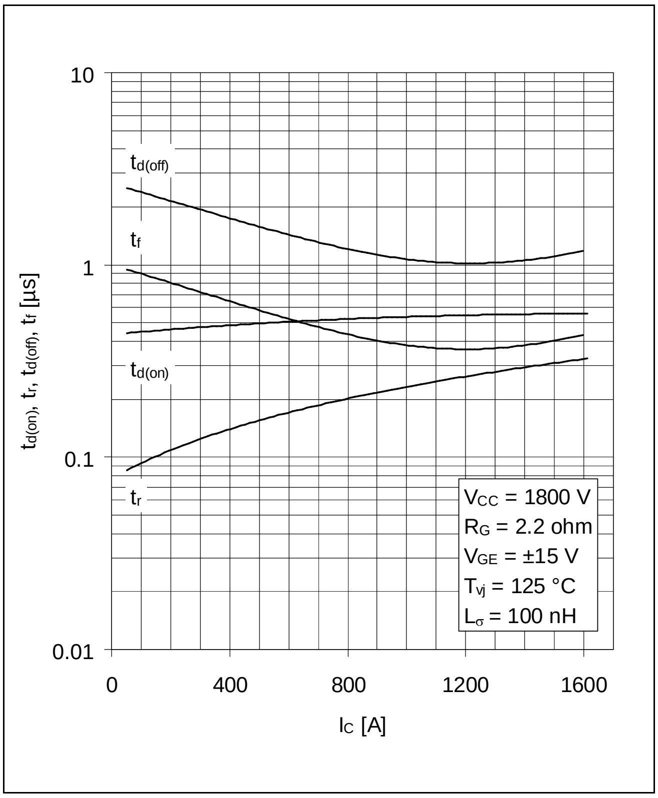


Fig. 5 Typical switching energies per pulse vs collector current

Fig. 6 Typical switching energies per pulse vs gate resistor



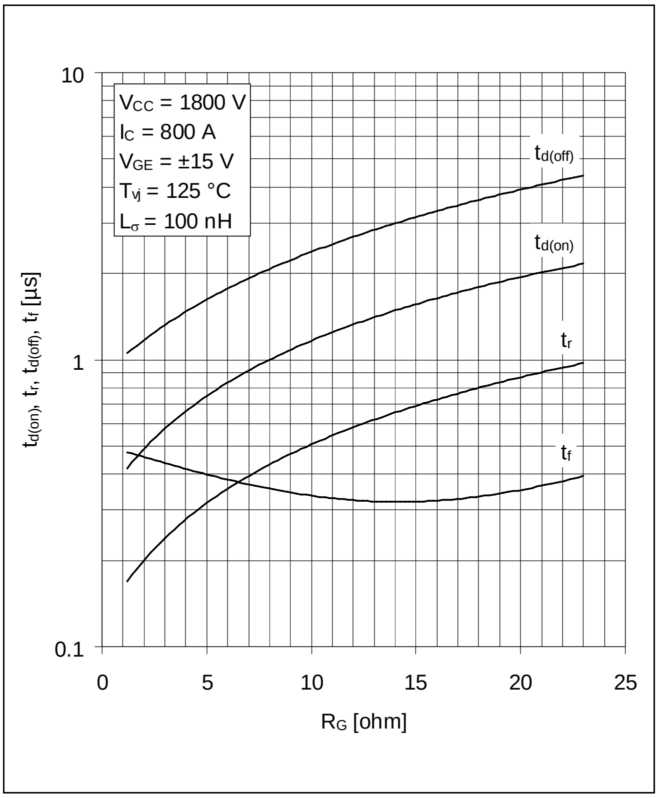


Fig. 7 Typical switching times vs collector current

Fig. 8 Typical switching times vs gate resistor

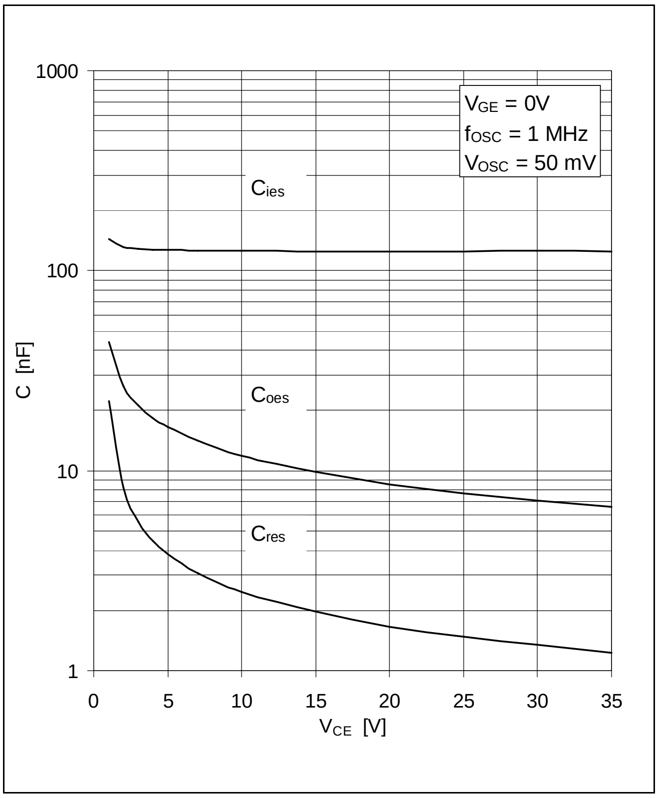


Fig. 9 Typical capacitances vs collector-emitter voltage

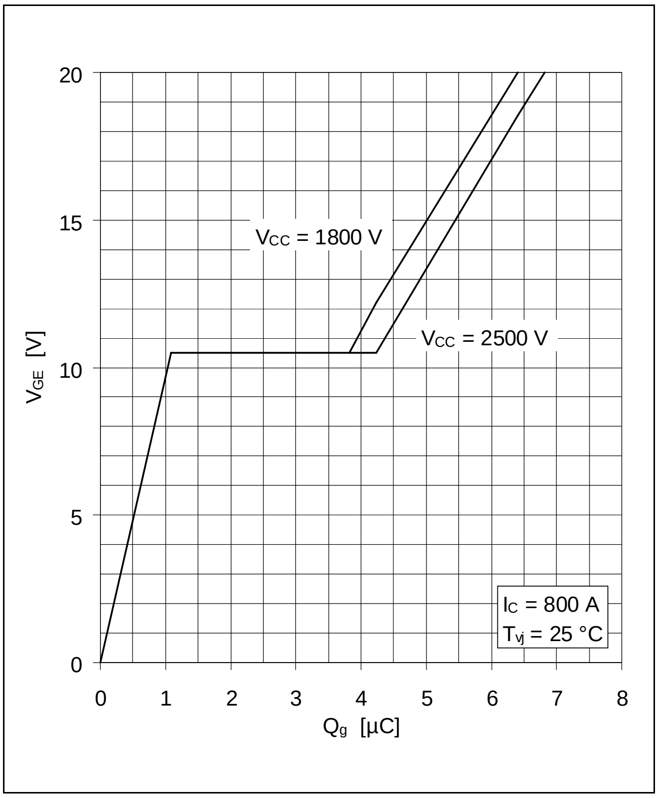


Fig. 10 Typical gate charge characteristics

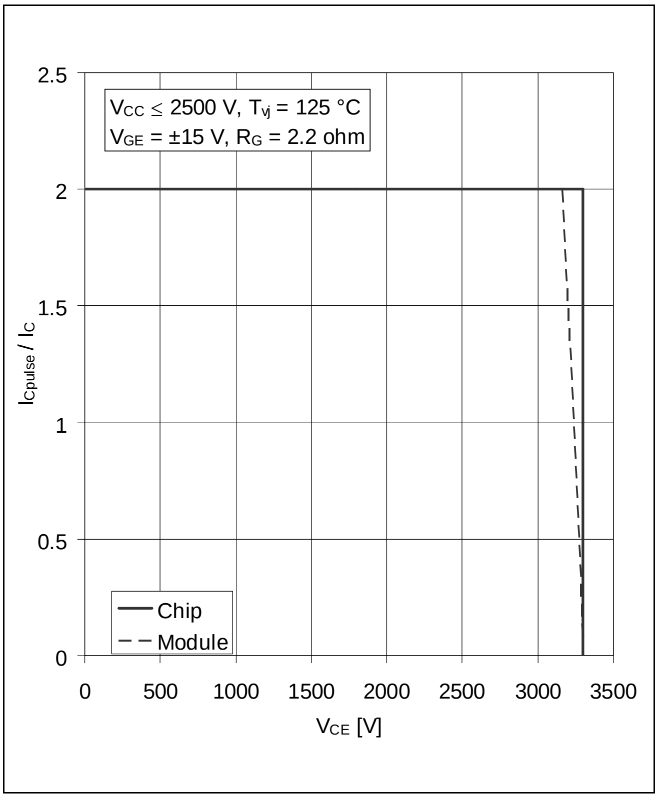


Fig. 11 Turn-off safe operating area (RBSOA)

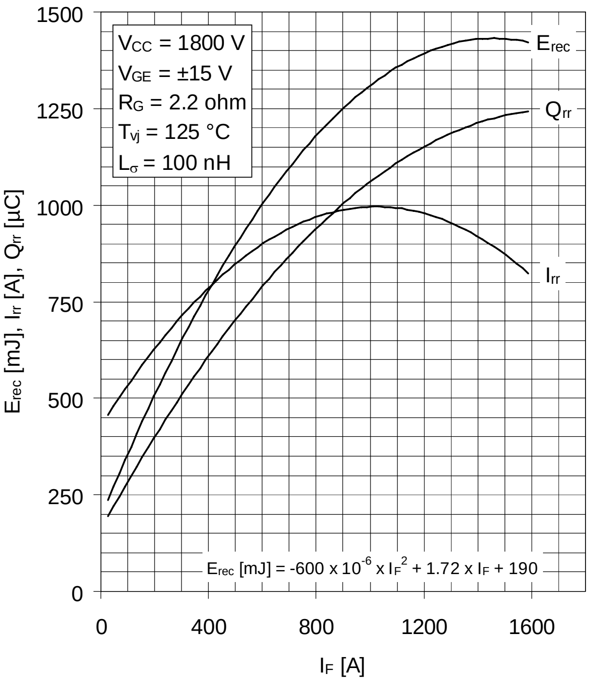


Fig. 12 Typical reverse recovery characteristics vs forward current

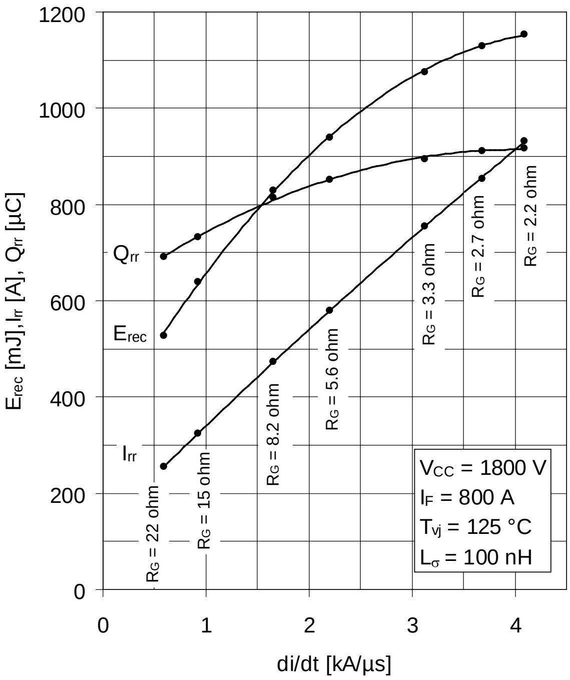


Fig. 13 Typical reverse recovery characteristics vs di/dt

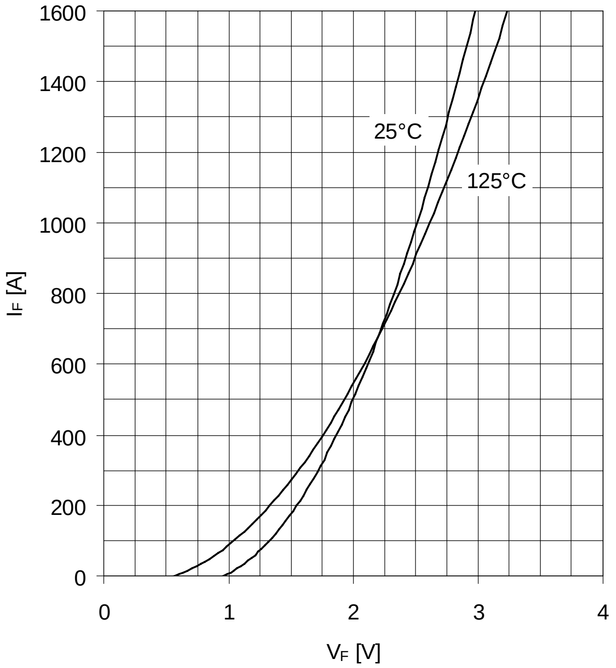


Fig. 14 Typical diode forward characteristics, chip level

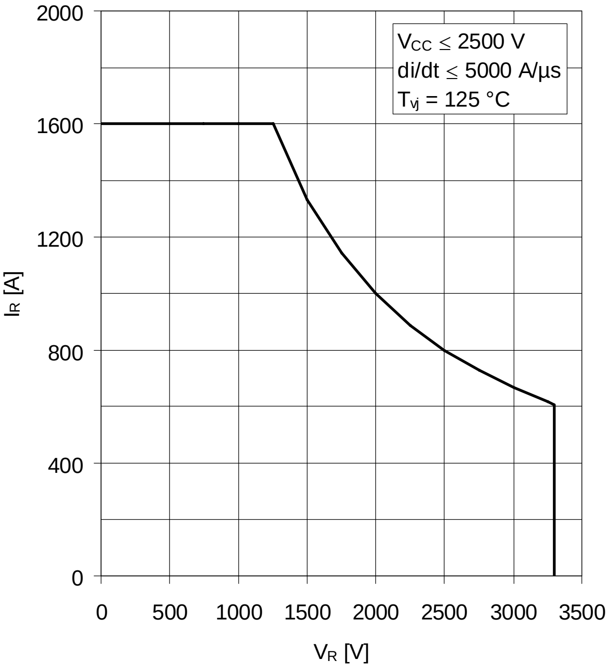


Fig. 15 Safe operating area diode (SOA)

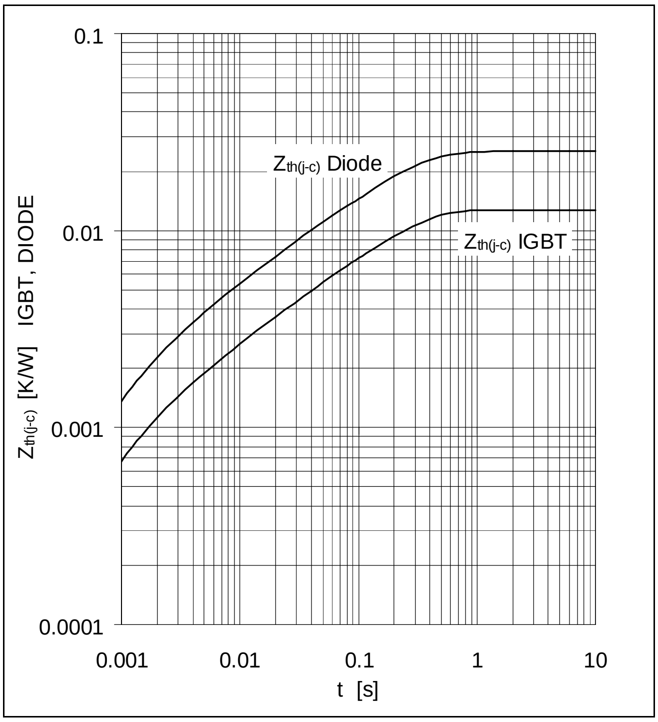


Fig. 16 Thermal impedance vs time

Analytical function for transient thermal impedance:

$$Z_{th\,(j\text{-}c)}(t) = \sum_{i=1}^{n} R_i\,(1 - e^{-t/\tau_i})$$

	i	1	2	3	4	
IGBT	R_i(K/kW)	8.78	2.06	0.961	0.948	
	τ_i(ms)	207.4	30.1	7.55	1.57	
DIODE	R_i(K/kW)	17.1	4.28	1.92	1.92	
	τ_i(ms)	203.6	30.1	7.53	1.57	

Related documents:

5SYA 2042 Failure rates of HiPak modules due to cosmic rays
5SYA 2043 Load – cycle capability of HiPaks
5SYA 2045 Thermal runaway during blocking
5SYA 2053 Applying IGBT
5SYA 2058 Surge currents for IGBT diodes
5SYA 2093 Thermal design of IGBT modules
5SYA 2098 Paralleling of IGBT modules
5SZK 9111 Specification of environmental class for HiPak Storage
5SZK 9112 Specification of environmental class for HiPak Transportation
5SZK 9113 Specification of environmental class for HiPak Operation (Industry)
5SZK 9120 Specification of environmental class for HiPak

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